

Finite band effects over the linear conductance through a quantum wire coupled with a quantum dot: X-boson treatment

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We study the electronic transport through a quantum wire (QW) with a strong side coupled quantum dot (QD). We obtain a linear conductance with lateral peaks when the gate voltage, is located near the edge of the conduction band. The calculated density of states shows, that these peaks are associated with renormalized localized levels out side of the conduction band. These results are compatibles with recent experimental results. *Key words* : Quantum Dot; Fano resonance; Mesoscopic system; X-boson.

In a previous work, we apply the X-boson method [1] for the single impurity case to describe the transport problem through a quantum wire (QW) with a side coupled quantum dot (QD), in the limit when the coulomb interaction at the QD was $U \rightarrow \infty$ [2]. In this work we apply the X-boson method to the same system studied in our previous work [2], but considering a stronger coupling between the QD and the QWW, in a similar situation described in a recent experimental work [3].

The model we use to describe the system is the Anderson impurity Hamiltonian in the $U \rightarrow \infty$ limit using the Hubbard operators representation, given by

$$H = \sum_{\mathbf{k},\sigma} E_{\mathbf{k},\sigma} c_{\mathbf{k},\sigma}^\dagger c_{\mathbf{k},\sigma} + \sum_{\sigma} E_{f,\sigma} X_{f,\sigma\sigma} \quad (1)$$

$$+ \sum_{\mathbf{k},\sigma} \left(V_{f,\mathbf{k},\sigma} X_{f,0\sigma}^\dagger c_{\mathbf{k},\sigma} + V_{f,\mathbf{k},\sigma}^* c_{\mathbf{k},\sigma}^\dagger X_{f,0\sigma} \right).$$

The first term represents the conduction electrons (c -electrons), associated with the wire. The second describes the QD and the last one corresponds to the interaction between the c -electrons and the QD. At low temperature and small

bias voltage, the electronic transport is coherent and a linear-conductance is obtained using the Landauer-type formula [2]

$$G = \frac{2e^2}{h} \int \left(-\frac{\partial n_F}{\partial \omega} \right) S(\omega) d\omega, \quad (2)$$

where n_F is the Fermi distribution function and $S(\omega)$ is the transmission probability of an electron with energy $\hbar\omega$, given by $S(\omega) = \Gamma^2 |G_{00}^\sigma|^2$. V is the matrix element connecting the QD with its nearest site, belonging to the wire, represented by the label 0, $\Gamma = V^2/\Delta$, with $\Delta = \frac{\pi V^2}{2W}$, W is the half-width conduction band and $G_{00}^\sigma(\omega)$ is the dressed Green function (GF) at the wire site 0. This function can be written in terms of the GF at the QD, G_{qd}^σ and the GF that describes the conduction electrons $g_c^\sigma(z) = -\frac{1}{2W} \ln \left| \frac{z+W}{z-W} \right|$ (ballistic channel), as $G_{00}^\sigma = (g_c^\sigma V)^2 G_{qd}^\sigma + g_c^\sigma$.

Using the chain X-boson method, and considering a constant density of states for the wire, $-W \leq \epsilon_{\mathbf{k}} \leq W$, the GF for the QD is given by [1,2]

$$G_{qd}^\sigma(z) = \frac{-D_\sigma}{z - \tilde{E}_f - \frac{V^2 D_\sigma}{2W} \ln \left| \frac{z+W}{z-W} \right|}, \quad (3)$$

where $z = \omega + i\eta$, the quantity $D_\sigma = \langle X_{0,0} \rangle + n_{f,\sigma}$

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is responsible for the correlation in the chain X-boson approach [1] and $\tilde{E}_f = E_f + \Lambda$, where Λ is a parameter of the X-boson method for the impurity case [1]. In the Fig. 1 we show the linear conductance G vs V_{gate} , associated with the energy E_f of the localized state (QD) in the experimental works [3], for a half-width band $W = 35\Delta$, with $\Delta = \frac{\pi V^2}{2W}$. It is possible to see the lateral resonances, when $V_{gate} = E_f$ is located near the edge of the conduction band, associated with the QW. Our numerical calculations show that these lateral peaks are absent for low temperatures.

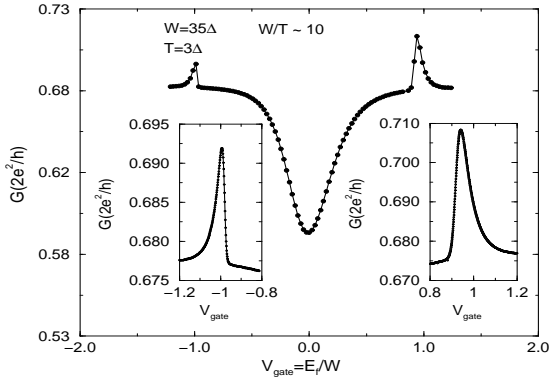


Figure 1. Conductance G vs $V_{gate} = E_f/W$. The maximum value of the linear conductance was taken from the maximum constant value (the “background”) for the linear conductance in the experimental result of Göres et. al. [3] in their Fig. 4-a. The insets show in detail the lateral resonances

In the Fig. 2 we present the density of states associated with the wire site 0, $\rho_{0\sigma}(\omega)$, and at the QD $\rho_{qd,\sigma}(\omega)$ respectively; the density of states $\rho_{c,\sigma}(\omega)$, associated with the undressed GF $g_c^\sigma(\omega)$, for a value of $V_{gate} = E_f > +W$ is also shown. It is possible to see the appearance of a localized level out of the conduction band. A similar level was obtained at the left side of the border of the conduction band. The inset present the same re-

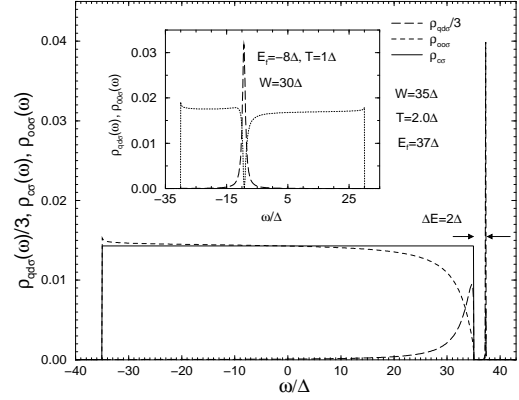


Figure 2. Density of states associated with the Green’s functions of the system.

sults, but for a value of $V_{gate} = E_f$ inside of the conduction band.

We obtain similar results to the measurements presented in the experimental work of Göres et. al [3] for the case of a single electron transistor (Fig 2a in [3]). In this work a small magnetic field (\vec{H}) was applied at a constant temperature, increasing one of the lateral peaks (Fig 6 in [3]). We expect that the presence of \vec{H} reduces the separation between the localized level and the nearest edge of the band for electrons with spin oriented in the opposite direction of \vec{H} , increasing the transport in the channel associated with this spin orientation. This process could exponentially increase the height of the peak associated with this conduction channel when \vec{H} is increased.

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